

WHAT IS CLAIMED IS:

Please revise the claims to read as follows:

1. (Presently Amended) A method for fabricating a transistor on a semiconductor substrate, comprising the steps of:

forming a first oxide layer on the substrate;

forming a second oxide layer on the substrate; and

forming a gate over the substrate;

wherein the first oxide layer and the second oxide layer form a composite oxide layer under the gate, the composite oxide layer being thicker near at least one end of a width of the gate.

2. (Presently Amended) The method of claim 1 wherein the step of forming the first oxide layer further comprises:

forming an initial oxide layer that uniformly covers an active area of the transistor;

and

etching away the initial oxide layer in most of the active area, leaving a ~~portions~~ portion of the initial oxide layer in a location over which a part the gate is formed.

3. (Original) The method of claim 2 wherein the step of etching away an area of the initial oxide layer to create the first oxide layer is performed using a low voltage mask that covers a portion of the active area near where an end of the gate is formed.

4. (Presently Amended) The method of claim 3 wherein the ~~portions~~ portion of the active area covered by the low voltage mask extends beyond sides of the gate.

5. (Original) The method of claim 1 further comprising forming lightly doped drain regions of the transistor by implanting dopants through the composite oxide layer, wherein the dopants are partially blocked or attenuated during the implant by the thicker composite oxide layer near an end of the gate.

6. (Original) The method of claim 1 further comprising forming spacers adjacent the gate.

7. (Original) The method of claim 1 further comprising forming source and drain regions of the transistor by implanting dopants through the composite oxide layer, wherein the dopants

are partially blocked or attenuated during the implant by the thicker composite oxide layer near an end of the gate.

8. (Presently Amended) The method of claim 1 wherein the step of forming the first oxide layer comprises;

placing a mask over the substrate, the mask covering most of an active area of the transistor, leaving exposed to an oxidation ambient a portion of the active area in a location over which a part of the gate is ~~[[formed.;]]~~ formed; and

oxidizing the substrate in the oxidation ambient to form the first oxide layer.

9. (Presently Amended) The method of claim 1 wherein the step of forming the second oxide layer further comprises;

placing a mask over the substrate, the mask covering most of an active area of the transistor, leaving exposed to an oxidation ambient a portion of the active area in a location over which a part of the gate is ~~[[formed.;]]~~ formed; and

oxidizing the substrate in the oxidation ambient to form the second oxide layer.

10. – 19. (Cancelled)

20. (New) A method for fabricating a transistor on a semiconductor substrate, comprising the steps of:

forming a first oxide layer on the substrate;

forming a second oxide layer on the substrate;

forming a gate over the substrate;

wherein the first oxide layer and the second oxide layer form a composite oxide layer under the gate, the composite oxide layer being thicker near at least one end of the gate; and

forming lightly doped drain regions in the substrate by implanting dopants through the composite oxide layer, wherein the dopants are partially blocked or attenuated during the implant by the thicker composite oxide layer near an end of the gate.

21. (New) A method for fabricating a transistor on a semiconductor substrate, comprising the steps of:

forming a first oxide layer on the substrate;

forming a second oxide layer on the substrate; and

forming a gate over the substrate extending between first and second isolation regions;

wherein the first oxide layer and the second oxide layer form a composite oxide layer under the gate, the composite oxide layer being thicker near at least one of the first and second isolation regions.